



# DV SERIES

6 to 10kV, 55 to 75mA, 75nS  
Axial Lead Low Current Diodes



## Features

- Subminiature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

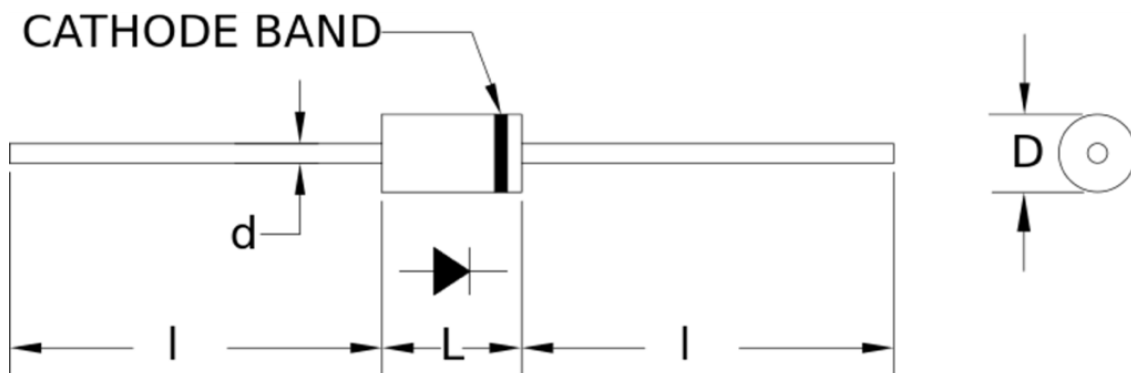
## Specifications<sup>1</sup>

Part Number	V <sub>R</sub> RM V	I <sub>F</sub> AVM mA	V <sub>F</sub> V	I <sub>R</sub> μA	I <sub>F</sub> SM A	C <sub>J</sub> pF	T <sub>RR</sub> nS	L in.	D in.	d in.	l in.
DV6P	6000	75	8.0	0.02	3	1.30	75	0.195	0.08	0.02	1.0
DV8P	8000	60	11.5	0.02	3	0.90	75	0.195	0.08	0.02	1.0
DV10P	10000	55	16.0	0.04	3	0.65	75	0.195	0.08	0.02	1.0

Temperature °C	
Operating Temperature	-55 to 150
Storage Temperature	-55 to 175
Maximum Junction Temperature	150

<sup>1</sup>25°C ambient temperature unless stated otherwise.

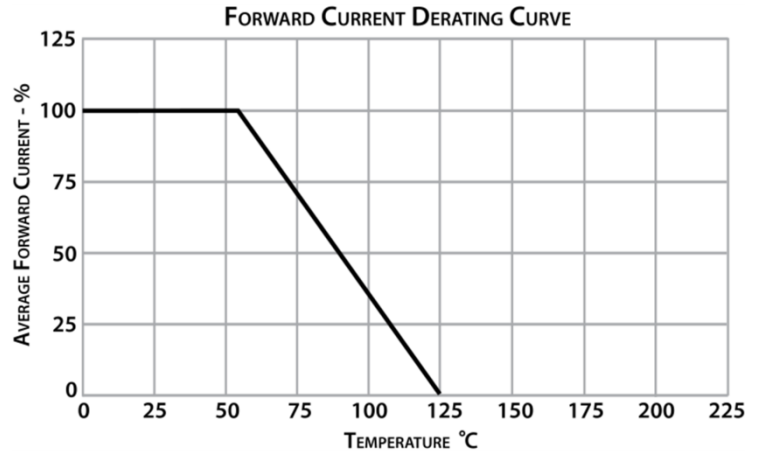
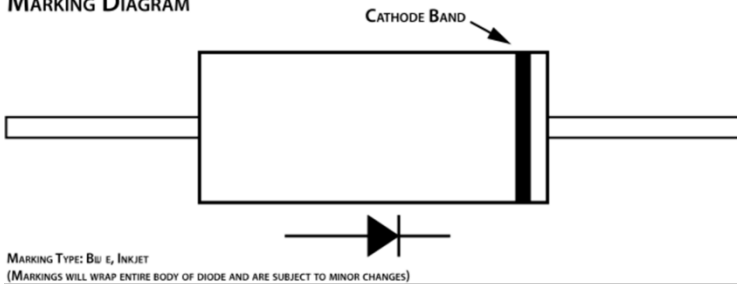
## Drawings<sup>2</sup>



<sup>2</sup>Dimensions in inches, tolerances ±0.020 except as noted



**MARKING DIAGRAM**



**Specification Definitions**

Specifications		Conditions
<b>V<sub>RRM</sub></b>	Maximum Repetitive Reverse Voltage	-
<b>I<sub>FAVM</sub></b>	Maximum Average Forward Current	At T <sub>A</sub> = 55°C
<b>V<sub>F</sub></b>	Maximum Forward Voltage Drop	At 20mA
<b>I<sub>R</sub></b>	Maximum Leakage Current	At V <sub>RRM</sub>
<b>I<sub>FSM</sub></b>	Maximum Surge Current	At 8.3mS, Single Half Sine
<b>C<sub>J</sub></b>	Typical Junction Capacitance	At V <sub>R</sub> = 0VDC, f = 1MHz
<b>T<sub>RR</sub></b>	Maximum Reverse Recovery Time	I <sub>F</sub> = 0.5 I <sub>FAVM</sub> ; I <sub>R</sub> = -I <sub>FAVM</sub> ; I <sub>RR</sub> = -0.25 I <sub>FAVM</sub>

Note: Specifications subject to change without notice. Photo is representation only.

